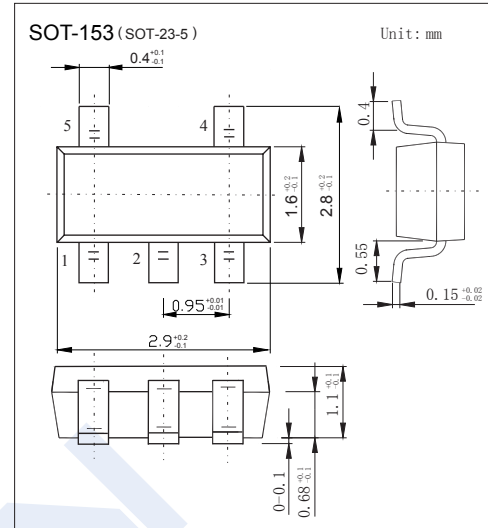
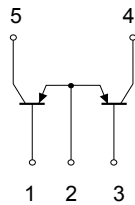


## PNP Transistors

## FMS3 (KMS3)

## ■ Features

- Collector Current Capability  $I_c = -50\text{mA}$
- Collector Emitter Voltage  $V_{CE0} = -120\text{V}$
- High breakdown voltage.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-120	V
Collector - Emitter Voltage	$V_{CE0}$	-120	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_c$	-50	mA
Collector Power Dissipation	$P_c$	300	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_c = -100\ \mu\text{A}, I_E = 0$	-120			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_c = -1\ \text{mA}, I_B = 0$	-120			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100\ \mu\text{A}, I_c = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -100\ \text{V}, I_E = 0$			-0.5	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -4\ \text{V}, I_c = 0$			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -10\ \text{mA}, I_B = -1\ \text{mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -10\ \text{mA}, I_B = -1\ \text{mA}$			-1.2	
DC current gain	$h_{FE}$	$V_{CE} = -6\ \text{V}, I_c = -2\ \text{mA}$	180		820	
Transition frequency	$f_T$	$V_{CE} = -12\ \text{V}, I_E = 2\ \text{mA}, f = 100\ \text{MHz}$		140		MHz

## ■ Marking

Marking	S3
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